

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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# 2SC1345(K)

Silicon NPN Epitaxial

**RENESAS**

ADE-208-1053 (Z)  
1st. Edition  
Mar. 2001

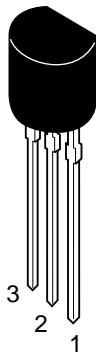
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## Application

Low frequency low noise amplifier

## Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

## 2SC1345 (K)

### Absolute Maximum Ratings (Ta = 25°C)

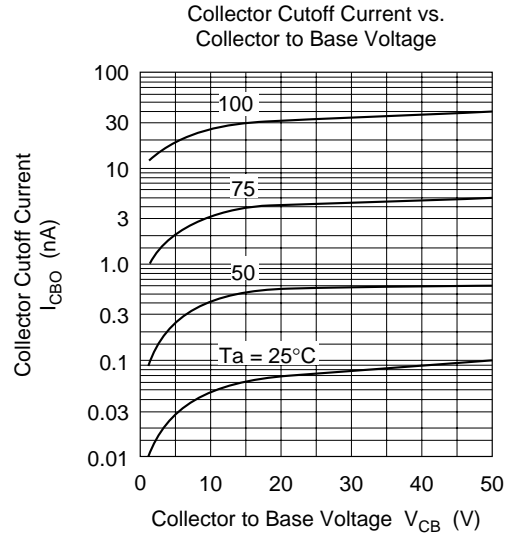
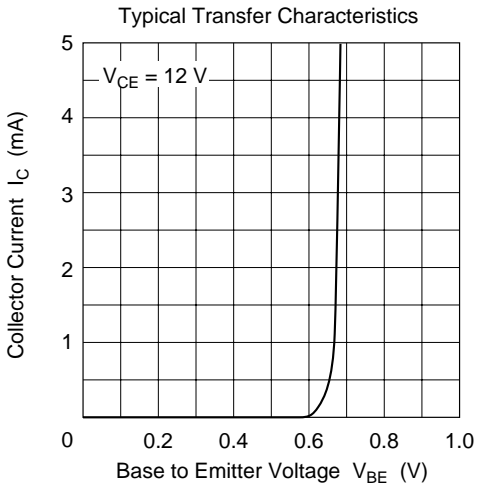
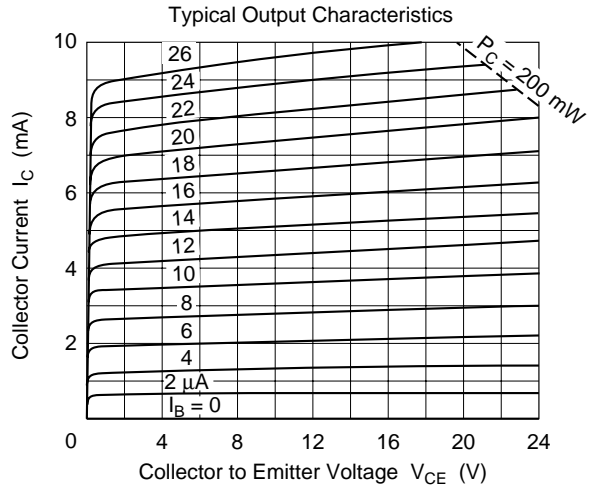
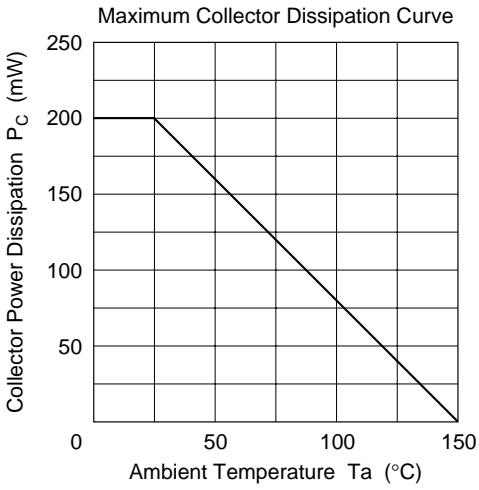
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	55	V
Collector to emitter voltage	$V_{CEO}$	50	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

### Electrical Characteristics (Ta = 25°C)

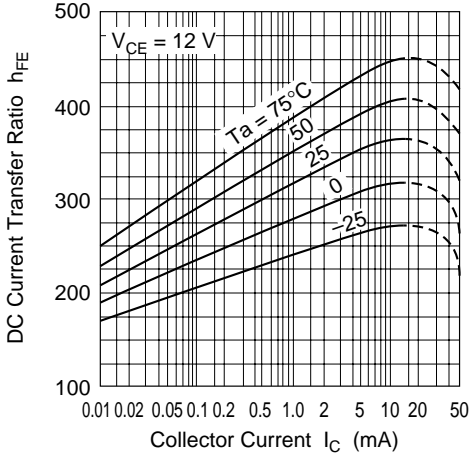
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	55	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB} = 18 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	0.5	$\mu A$	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	250	—	1200		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Base to emitter voltage	$V_{BE}$	—	—	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Collector output capacitance	$C_{ob}$	—	2.3	3.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Gain bandwidth product	$f_T$	—	230	—	MHz	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Noise figure	NF	—	—	8	dB	$V_{CE} = 6 \text{ V}, I_C = 0.1 \text{ mA},$ $f = 10 \text{ Hz}, R_g = 10 \text{ k}\Omega$
				1		$V_{CE} = 6 \text{ V}, I_C = 0.1 \text{ mA},$ $f = 1 \text{ kHz}, R_g = 10 \text{ k}\Omega$

Note: 1. The 2SC1345(K) is grouped by  $h_{FE}$  as follows.

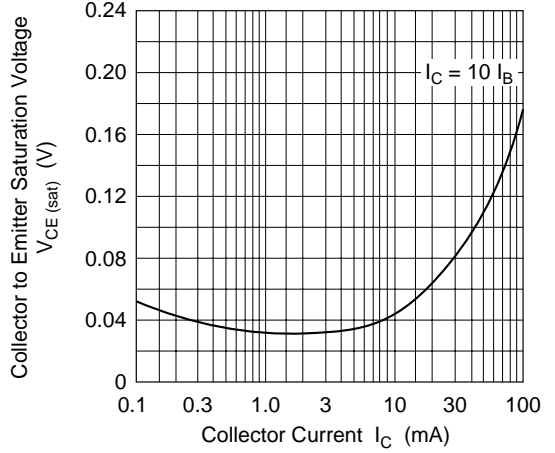
D	E	F
250 to 500	400 to 800	600 to 1200



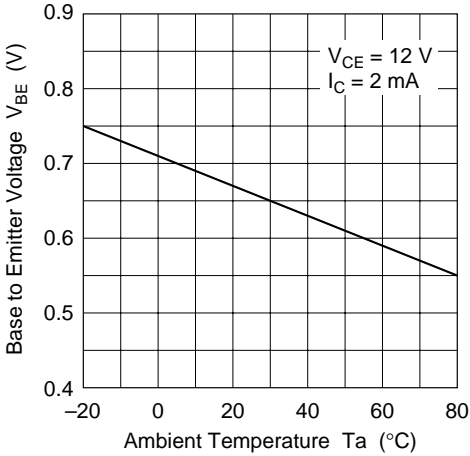
DC Current Transfer Ratio vs. Collector Current



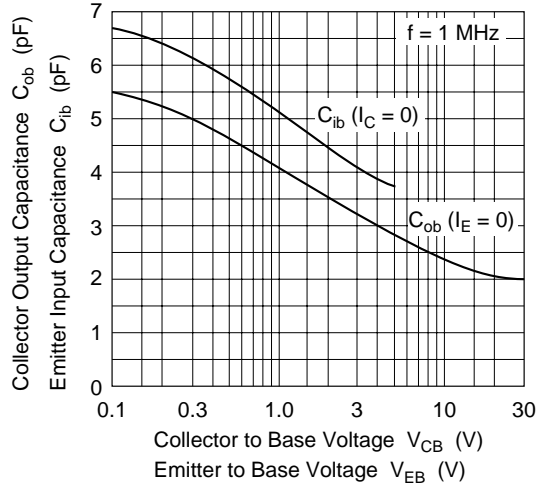
Collector to Emitter Saturation Voltage vs. Collector Current



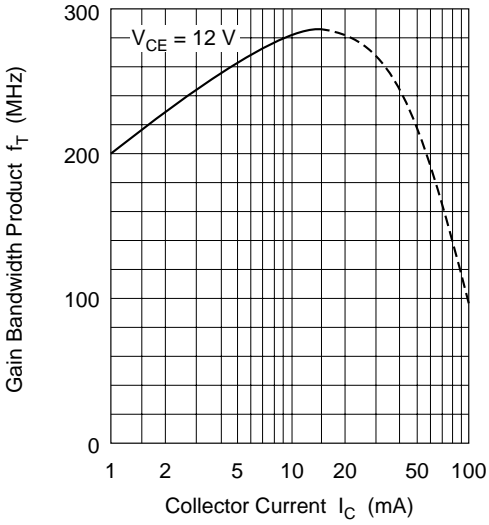
Base to Emitter Voltage vs. Ambient Temperature



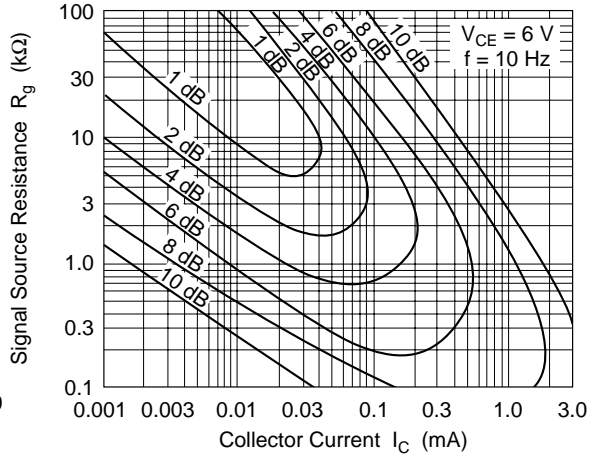
Input and Output Capacitance vs. Voltage



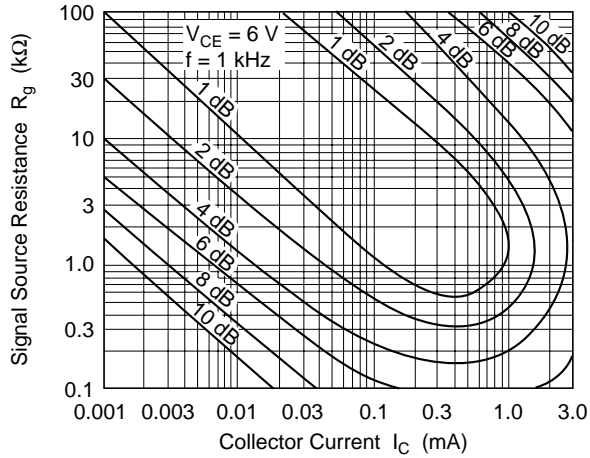
Gain Bandwidth Product vs. Collector Current

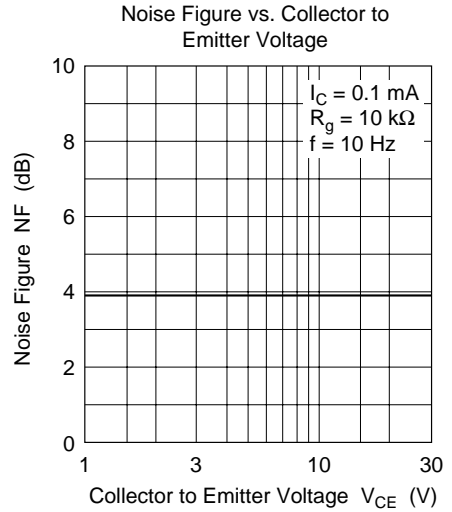
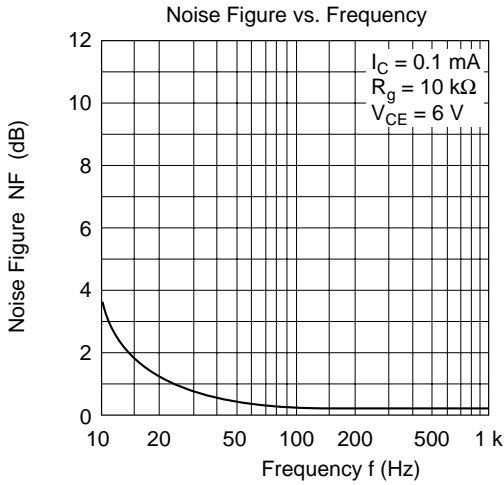
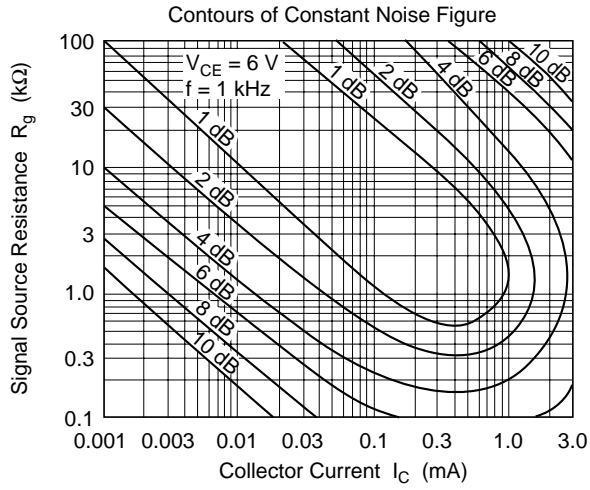


Contours of Constant Noise Figure

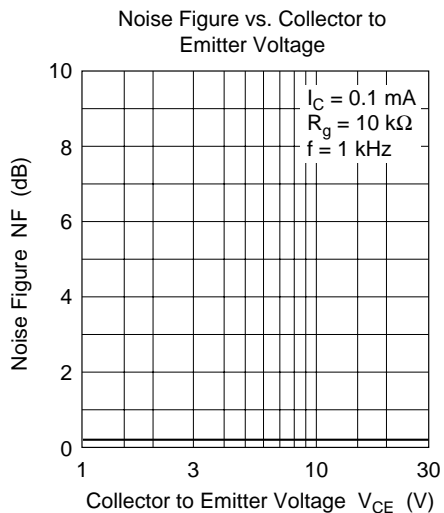
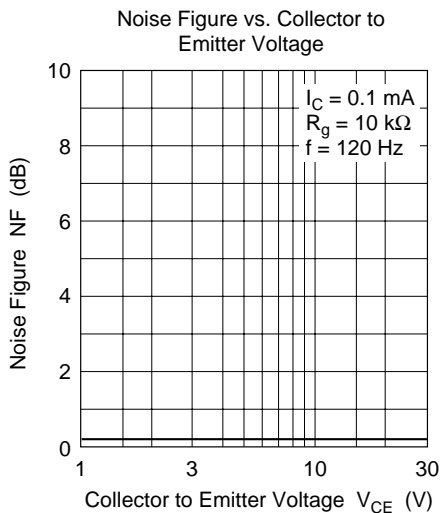


Contours of Constant Noise Figure





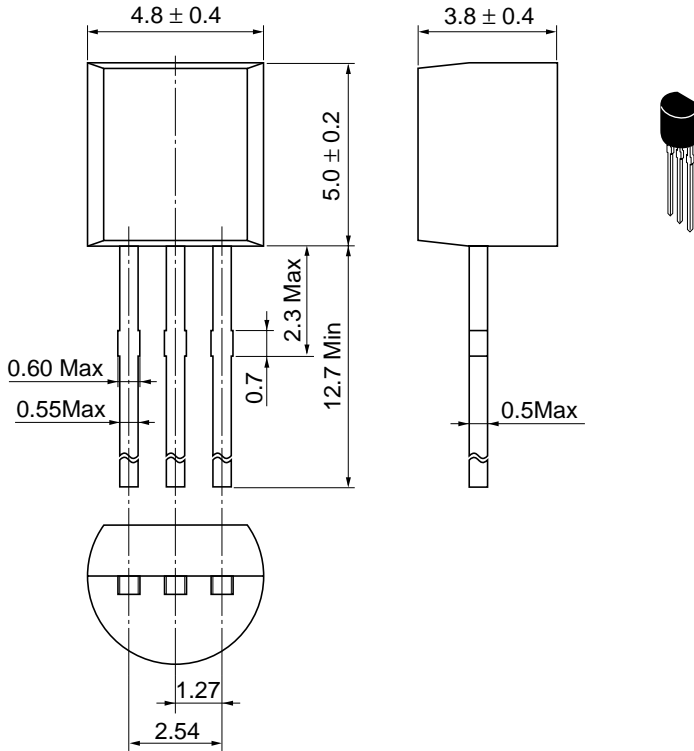




## Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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